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Sheet 1 of 2

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE	ATTY. DOCKET NO.	SERIAL NO
	PATENT AND TRADEMARK OFFICE	9138-0064(CIP)	09/981,024
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	APPLICANT Tsong, et al.		
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U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
					YES <input type="checkbox"/> NO <input checked="" type="checkbox"/>

OTHER DOCUMENTS (Including Author, Title, Date Pertinent Pages, Etc.)

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MAA	Goldfarb, The Journal of Chemical Physics, "Infrared Spectrum and Structure of Germyl Cyanide", Vol. 37, No. 3, pgs. 642-646 (1962)
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EXAMINER

Matthew Anderson

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